

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSIII⁵)

2SK1544

DC-DC Converter and Motor Drive Applications

- Low drain-source ON resistance : $R_{DS(ON)} = 0.15 \Omega$ (typ.)
- High forward transfer admittance : $|Y_{fs}| = 21 \text{ S}$ (typ.)
- Low leakage current : $I_{DSS} = 300 \mu\text{A}$ (max) ($V_{DS} = 500 \text{ V}$)
- Enhancement-mode : $V_{th} = 1.5 \sim 3.5 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	500	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	500	V
Gate-source voltage		V_{GSS}	± 30	V
Drain current	DC (Note 1)	I_D	25	A
	Pulse (Note 1)	I_{DP}	100	
Drain power dissipation ($T_c = 25^\circ\text{C}$)		P_D	200	W
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	$-55 \sim 150$	$^\circ\text{C}$

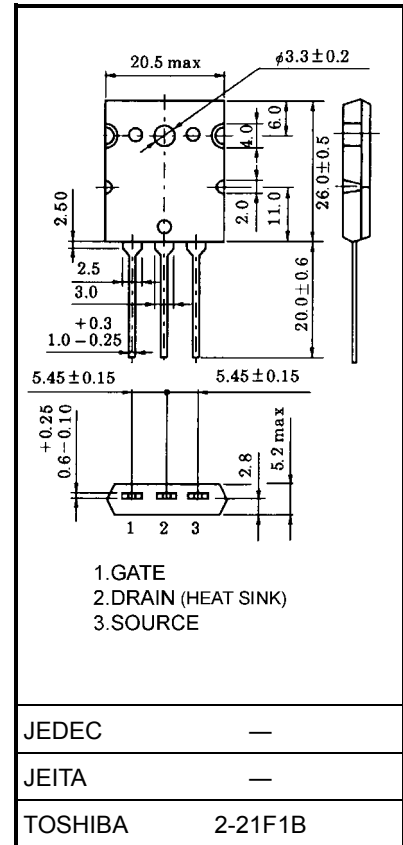
Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	0.625	$^\circ\text{C} / \text{W}$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	35.7	$^\circ\text{C} / \text{W}$

Note 1: Please use devices on condition that the channel temperature is below 150°C .

This transistor is an electrostatic sensitive device.
Please handle with caution.

Unit: mm



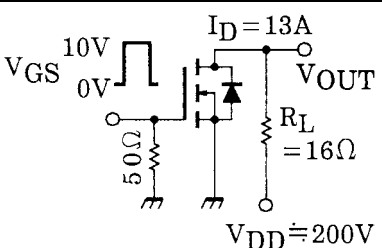
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TOSHIBA 2-21F1B

Weight: 9.75 g (typ.)

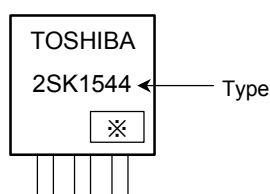
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 100	nA
Drain cut-off current		I_{DSS}	$V_{DS} = 500 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	300	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	500	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	1.5	—	3.5	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 13 \text{ A}$	—	0.15	0.20	Ω
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 13 \text{ A}$	10	21	—	S
Input capacitance		C_{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	3700	—	pF
Reverse transfer capacitance		C_{rss}		—	400	—	
Output capacitance		C_{oss}		—	920	—	
Switching time	Rise time	t_r		—	185	—	ns
	Turn-on time	t_{on}		—	240	—	
	Fall time	t_f		—	250	—	
	Turn-off time	t_{off}		—	590	—	
Total gate charge (Gate-source plus gate-drain)		Q_g	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 25 \text{ A}$	—	150	—	nC
Gate-source charge		Q_{gs}		—	70	—	
Gate-drain ("miller") charge		Q_{gd}		—	80	—	



Source-Drain Ratings and Characteristics (Ta = 25°C)

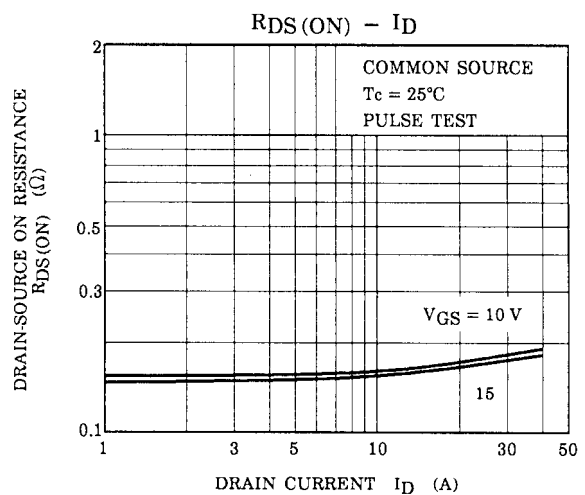
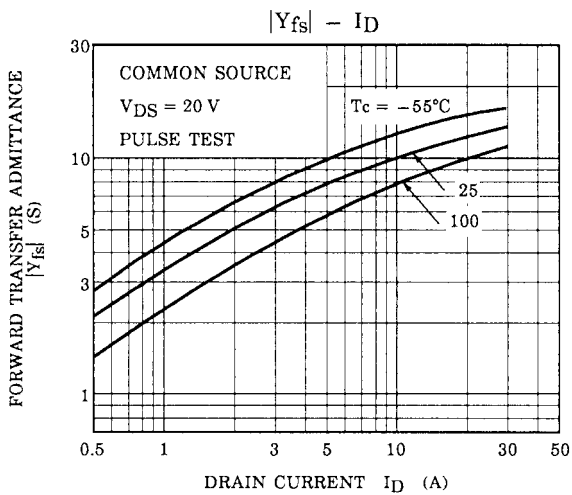
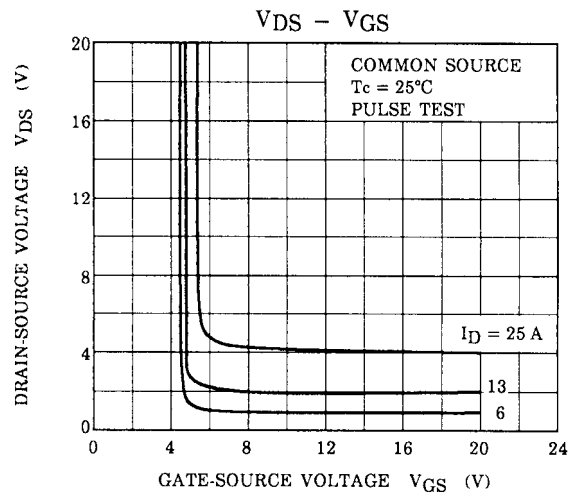
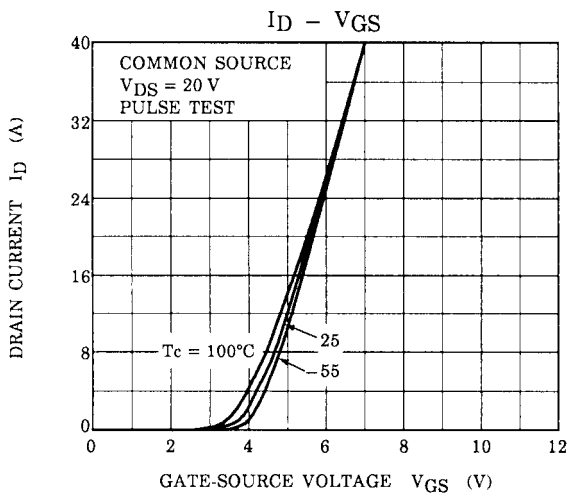
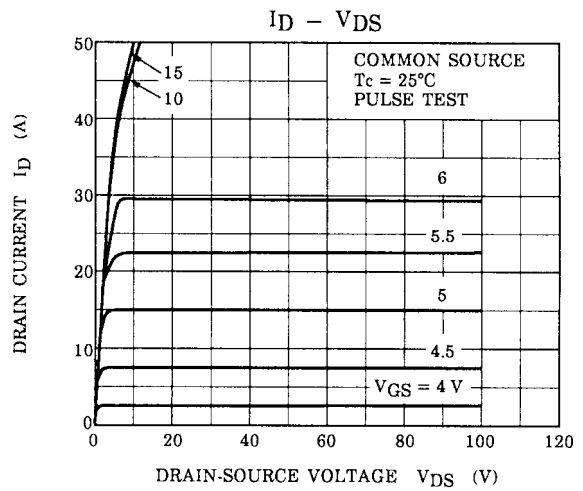
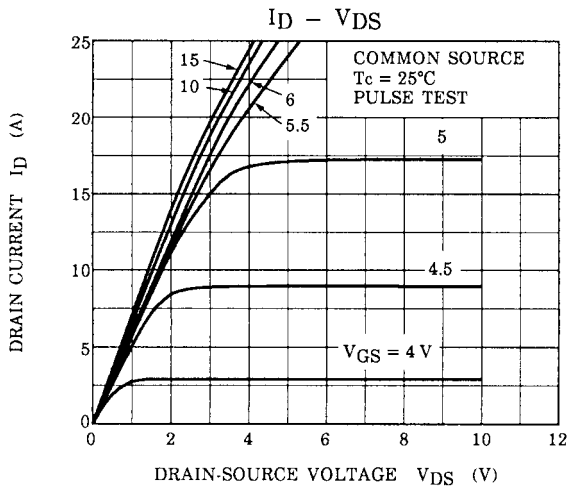
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	25	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	100	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 25 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.6	V
Reverse recovery time	t_{rr}	$I_{DR} = 25 \text{ A}, V_{GS} = 0 \text{ V}$ $dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	780	—	ns
Reverse recovered charge	Q_{rr}		—	9.8	—	μC

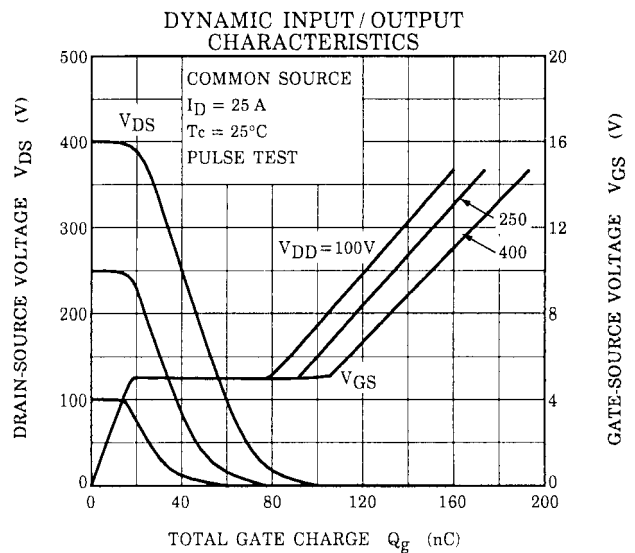
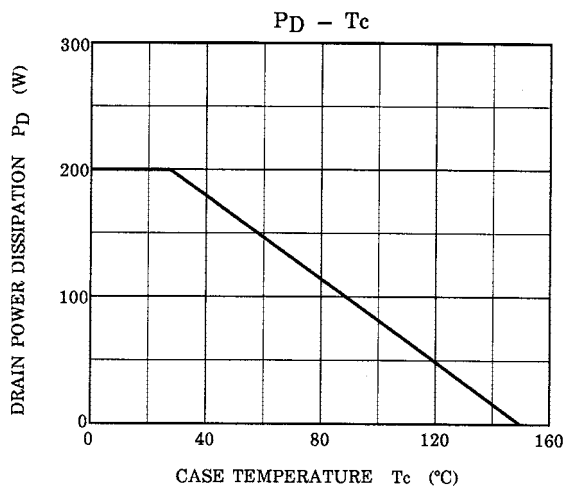
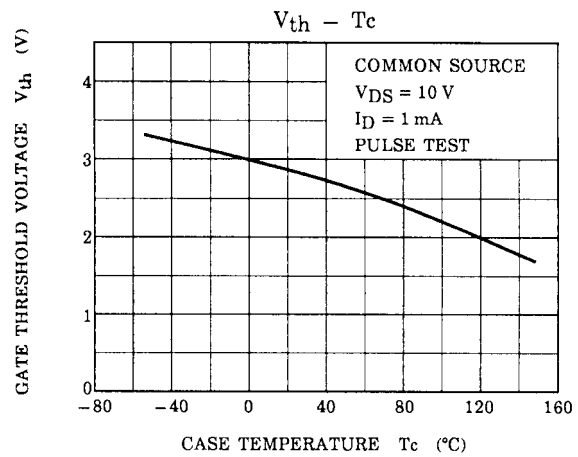
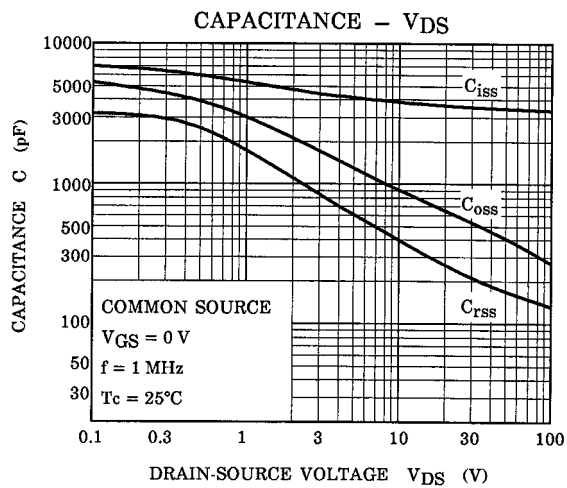
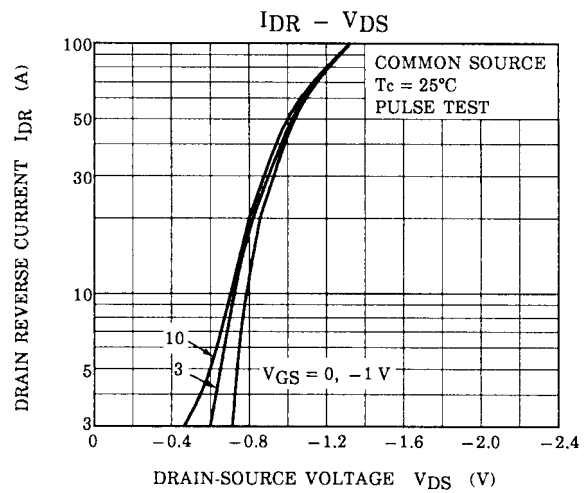
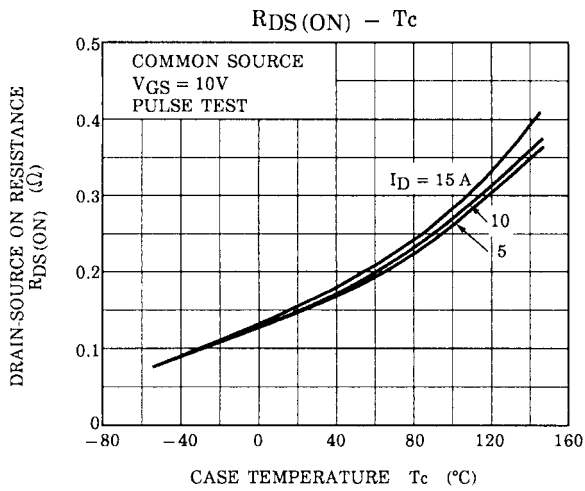
Marking

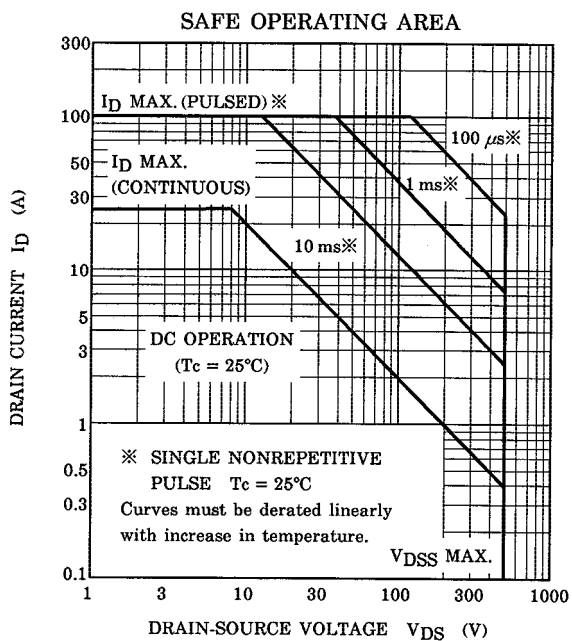
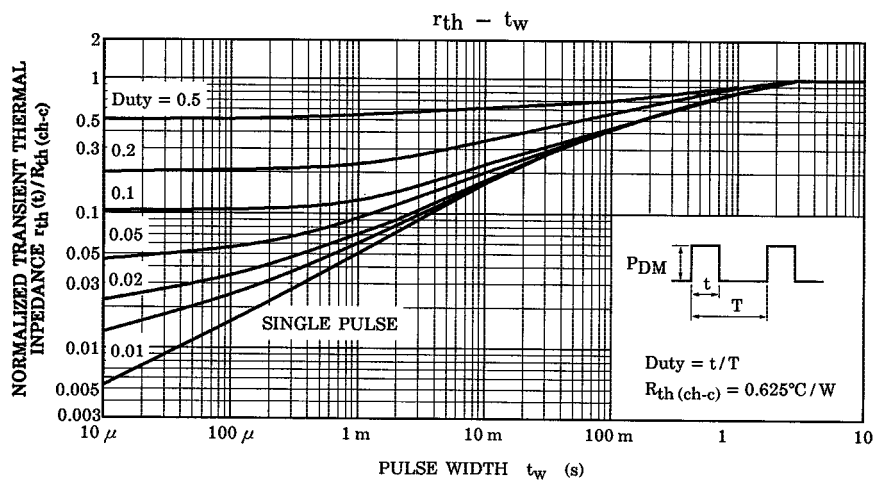


※ Lot Number



 Month (starting from alphabet A)
 Year (last number of the christian era)







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